Vishay Semiconductors



Small Signal Schottky Diode

Features

- For general purpose applications
- This diode features low turn-on voltage and high breakdown voltage. This device is protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges
- This diode is also available in a MiniMELF case with type designation LL41
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

Mechanical Data

Case: DO35 Glass Case

Weight: approx. 125 mg

Cathode Band Color: black

Packaging Codes/Options:

TR/10 k per 13" reel (52 mm tape), 50 k/box TAP/10 k per Ammopack (52 mm tape), 50 k/box

Parts Table

Part	Ordering code	Type Marking	Remarks	
BAT41	BAT41-TR or BAT41-TAP	BAT41	Tape and Reel/Ammopack	

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Repetitive peak reverse voltage		V _{RRM}	100	V
Forward continuous current	T _{amb} = 25 °C	١ _F	100 ¹⁾	mA
Repetitive peak forward current	t_p < 1 s, δ < 0.5, T_{amb} = 25 °C	I _{FRM}	350 ¹⁾	mA
Surge forward current	t _p = 10 ms, T _{amb} 25 °C	I _{FSM}	750 ¹⁾	mA
Power dissipation	T _{amb} = 65 °C	P _{tot}	200 ¹⁾	mW

¹⁾ Valid provided that electrodes are kept at ambient temperature



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Thermal Characteristics

 $T_{amb} = 25 \ ^{\circ}C$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction to ambient air		R _{thJA}	300 ¹⁾	K/W
Junction temperature		Tj	125	°C
Ambient operating temperature range		T _{amb}	- 65 to + 125	°C
Storage temperature range		T _{stg}	- 65 to + 150	°C

¹⁾ Valid provided that electrodes are kept at ambient temperature

Electrical Characteristics

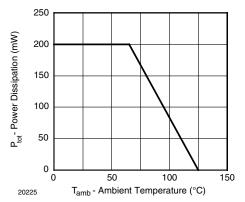
 $T_{amb} = 25 \ ^{\circ}C$, unless otherwise specified

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Reverse breakdown voltage ²⁾	I _R = 100 μA	V _(BR)	100	110		V
Leakage current ²⁾	V_R = 50 V, T_j = 25 °C	I _R			100	nA
	V _R = 50 V, T _j = 100 °C	I _R			20	μA
Forward voltage ²⁾	I _F = 1 mA	V _F		400	450	mV
	I _F = 200 mA	V _F			1000	mV
Diode capacitance	V _R = 1 V, f = 1 MHz	CD		2		pF

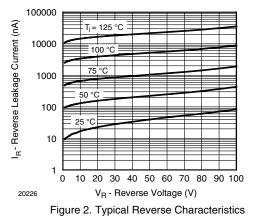
²⁾ Pulse test, $t_p = 300 \ \mu s$

Typical Characteristics

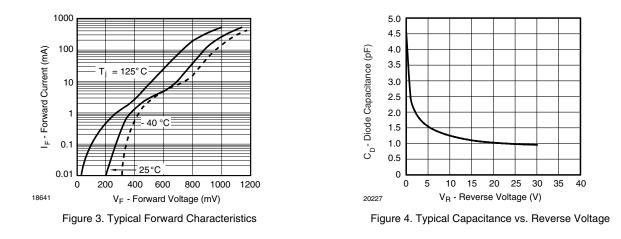
 $T_{amb} = 25$ °C, unless otherwise specified



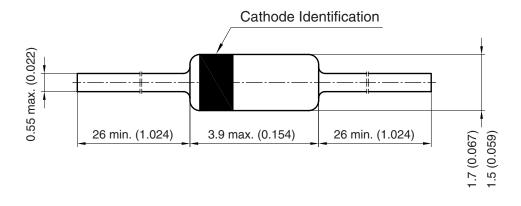








Package Dimensions in millimeters (inches): DO35



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Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



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